

$V_{\text{DRM}} = 4.5 \text{ kV}$
 $V_{\text{RRM}} = 18 \text{ V}$
 $I_{\text{PULSE}} = 110 \text{ kA}$
 $V_{\text{Dcmax}} = 2.8 \text{ kV}$

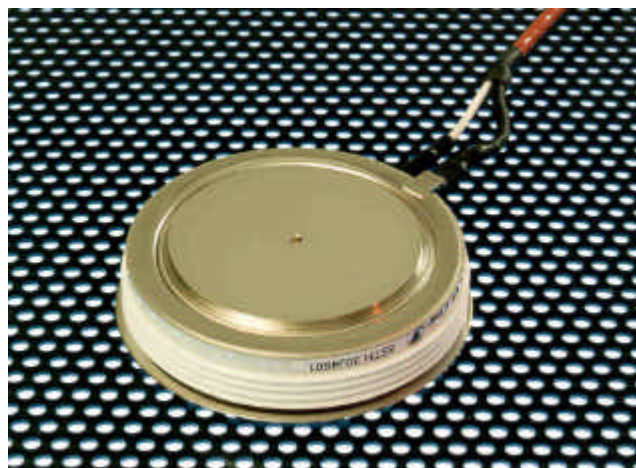
High Current High di/dt Switch for Pulsed Power Applications

5STH 30J4501

Doc. No. 5SYA 08PP-01 Oct. 01

Features

- Asymmetric Design
- For Single or Repetitive Pulse Applications
- Very High di/dt Capability
- Free Floating Silicon Technology
- Glazed Ceramic Presspack Housing
- High Interdigitated Gate Structure
- Optimized as Closing Switch
- High Reliability



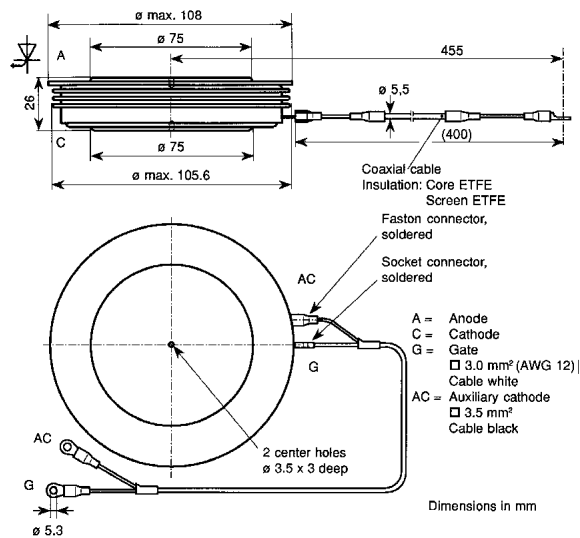
Electrical Data

V_{DRM}	Repetitive peak of-state voltage	4.5 kV	$T_j = 125^\circ\text{C}$
V_{RRM}	Repetitive reverse blocking voltage	18 V	$T_j = 125^\circ\text{C}$
V_{DC}	Permanent DC voltage for 100 FIT failure rate	2.8 kV	At $T_j \leq 125^\circ\text{C}$. Ambient cosmic radiation at sea level in open air.
I_{PULSE}	Max. Pulse Current	110 kA	Half sine wave, $T_j \leq 50^\circ\text{C}$, $t_p \leq 250 \mu\text{s}$
dt/dt	Max. current rate of rise	20 kA/ μs	1 Hz
V_{GT}	Max. Gate trigger voltage	4.0 V	diG/dt (min) 100 A/ μs $T_j = 25^\circ$ $T = 20 \mu\text{s}$
I_{GT}	Recomm. Gate trigger current	120 A	
I^2t	Limiting load integral	$1.5 \times 10^6 \text{ A}^2\text{s}$	$T_p = 250 \mu\text{s}$, $T_j = 50^\circ\text{C}$
V_{T0}	Threshold voltage	1.24 V	$T_j = 50^\circ\text{C}$ / $T_j = 125^\circ\text{C}$
r_T	Slope resistance	0.28 m Ω 0.30 m Ω	$T_j = 50^\circ\text{C}$ $T_j = 125^\circ\text{C}$
V_T	Voltage Drop	2.08 V 2.15 V	$T_j = 50^\circ\text{C}$, $I_r = 3000\text{A}$ $T_j = 125^\circ\text{C}$, $I_r = 3000\text{A}$
T_{Don}	Turn-on delay time	$\leq 0.9 \mu\text{s}$	

Pulse Power Device 5STH 30J4501

Mechanical Data

F_M	Mounting force	min.	36 kN
		max.	44 kN
D_p	Pole-piece diameter		75 mm
H	Housing thickness		26 mm
M	Weight		1,5 kg
D_s	Surface creepage distance		33 mm
D_a	Air strike distance		15 mm



Thermal Data

T_A	Ambient Temp.	min.	- 40 °C
		max.	125 °C
$T_{vj\text{m}}$	Max. Junction Temperature		125 °C
R_{thJC}	Thermal resistance junction - case		0.022 K/W (anode side cooling)
			0.027 K/W (cathode side cooling)
			0.012 K/W (double side cooling)
R_{thCH}	Thermal resistance case – heatsink		0.006 K/W (one side cooled)
			0.003 K/W (double side cooled)



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